

APPENDIX

Changes to Claims:

The following are marked-up versions of the amended claims:

4. (Amended) A tunnel magnetoresistive effective element as defined in claim 2 ~~or 3~~, wherein the second conductive layer includes a second electrode/magnetic shielding portion and a second leading electrode portion, and the second electrode/magnetic shielding portion is provided on the other surface of the ferromagnetic tunnel effective film, and the second leading electrode portion is electrically conducted to a part of the second electrode/magnetic shielding portion at a position in which a magnetic field having the same direction as that of the bias magnetic field is generated by a sense current in the second electrode/magnetic shielding portion.

6. (Amended) A tunnel magnetoresistive effective element as defined in claim 4 ~~or 5~~, wherein the first leading electrode portion and the second leading electrode portion are provided in respective different sides from the center line of the ferromagnetic tunnel effective film.

7. (Amended) A tunnel magnetoresistive effective element as defined in claim 4 ~~or 5~~, wherein the first leading electrode portion and the second leading electrode portion are provided in either side from the center line of the ferromagnetic tunnel effective film.

8. (Amended) A tunnel magnetoresistive effective element as defined in claim 6 ~~or 7~~, wherein a planer angle of a line segment to a first center point of a boundary line between the first electrode/magnetic shielding portion and the first leading electrode portion from a center point of the ferromagnetic tunnel effective film for the bias magnetic field direction or a planer angle of a line segment to a second

center point of a boundary line between the second electrode/magnetic shielding portion and the second leading electrode portion from the center point of the ferromagnetic tunnel effective film for the bias magnetic field direction is set to 5 degrees or over.

9. (Amended) A tunnel magnetoresistive effective element as defined in ~~any one of claims 1-8~~, claim 1, wherein the magnetic bias means includes a bias magnetic field-inductive layer to apply a given bias magnetic field to the free layer of the ferromagnetic tunnel effective film and a magnetic bias applying means to apply a given magnetic field to the bias magnetic field-inductive layer.

12. (Amended) A thin film magnetic head comprising at least one reading element composed of a tunnel magnetoresistive effective element as defined in ~~any one of claims 1-11~~, claim 1.

16. (Amended) A magnetic head device comprising a thin film magnetic head as defined in ~~any one of claims 12-15~~ claim 12 and a head supporting device to support the thin film magnetic head.